



INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

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Applicant(s)

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Not Yet Assigned

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL
Jagannathan, et al., "Self-aligned SiGe NPN Transistors with 285 GHz f_{MAX} and 207 GHz f_T in a Manufacturable Technology". IEEE Electron Device letters 23, 259 (2002)

J.S. Rieh, et al., "SiGe HBTs with Cut-off Frequency of 350 GHz", International Electron Device Meeting Technical Digest, 771 (2002)

M.W. Xu et al. "Ultra Low Power SiGe:C HBT for 0.18 um RF-FiCMOS, " Proceedings of the IEEE International Electron Devices Meeting, 2003.

EXAMINER

DATE CONSIDERED

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.